

What is claimed is:

1. A semiconductor package comprising:

an electrically insulating substrate layer;

5       a non-conductive layer disposed on the electrically insulating substrate layer; and,

a reflector layer disposed on the non-conductive layer.

2. The semiconductor package of claim 1, wherein the reflector layer includes a conical

portion.

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3. The semiconductor package of claim 1, wherein the electrically insulating layer includes at least one metallized portion on a first surface thereof.

4. The semiconductor package of claim 3, wherein the electrically insulating layer includes at

15       least one metallized portion on a second surface thereof, said second surface opposite said first surface.

5. The semiconductor package of claim 1, wherein the reflector layer is made of a material

with a coefficient of thermal expansion which is matched to a coefficient of thermal

20       expansion of a material of the electrically insulating substrate layer.

6. The semiconductor package of claim 1, wherein the non-conductive layer is made of glass.

7. The semiconductor package of claim 6, wherein the glass has a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

5       8. The semiconductor package of claim 7, wherein the glass and the material of the electrically insulating substrate layer both have a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the reflector layer.

9. A method for producing a semiconductor package, comprising the steps of:

10       applying a non-conductive layer to a metal reflector layer; and,  
             applying an electrically insulating layer including at least one metallized area to the non-conductive layer.

10. The method of claim 9, comprising the further step of:

15       coupling a light emitting diode to the electrically insulating layer.

11. The method of claim 9, wherein the at least one metallized area is formed by thin film metallization.

20       12. The method of claim 9, wherein the at least one metallized area is formed by thick film metallization.

13. The method of claim 9, wherein the step of applying an electrically insulating layer to the non-conductive layer comprises applying an electrically insulating layer including at least

one first metallized area on a first side thereof and at least one second metallized area on a second side opposite the first side.

14. A light emitting device comprising:

5       an electrically insulating substrate layer with at least one light emitting diode disposed thereon;

          a non-conductive layer disposed on the electrically insulating substrate layer; and,  
          a reflector layer disposed on the non-conductive layer.

10      15. The light emitting device of claim 14, wherein the electrically insulating layer further comprises at least one metallized portion which is coupled to the light emitting diode.

16. The light emitting device of claim 14, further comprising a lens disposed in a conical recess in the reflector layer.

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17. The light emitting device of claim 16, wherein the lens lies overtop of the at least one light emitting diode.